### PATENT COOPERATION TREATY

## **PCT**

# TRANSLATION INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY (Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

Applicant's or B14415	agent's file reference	FOR FURTHER A	CTION	See Form PCT/IPEA/416								
International a		International filing da	nte (day/month/vear)	Priority date (day/month/year)								
	2004/050433	15.09.200	, ,	17.09.2003								
International Patent Classification (IPC) or national classification and IPC												
G03F7/00												
Applicant COMMISSARIAT A L'ENERGIE ATOMIQUE												
<ol> <li>This report is the international preliminary examination report, established by this International Preliminary Examining Authority under Article 35 and transmitted to the applicant according to Article 36.</li> </ol>												
2. This	REPORT consists of a total	l of <b>8</b>	sheets, including	g this cover sheet.								
3. This	report is also accompanied	by ANNEXES, comprising:										
ا ۽ ا	(sent to the applican	nt and to the International Ri	reau) a total of	sheets as follows:								
	a. (sent to the applicant and to the International Bureau) a total of sheets, as follows:  sheets of the description, claims and/or drawings which have been amended and are the basis for this report and/or sheets containing rectifications authorized by this Authority (see Rule 70.16 and Section 607 of the Administrative Instructions).											
	sheets which supersede earlier sheets, but which this Authority considers contain an amendment that goes beyond the disclosure in the international application as filed, as indicated in item 4 of Box No. I and the Supplemental Box.											
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	, containing a sequence listing and/or tables related thereto, in computer readable form only, as indicated in the Supplemental Box Relating to Sequence Listing (see Section 802 of the Administrative Instructions).											
4. This	report contains indications	relating to the following iter	ms:									
	Box No. I Basis	of the report										
	Box No. II Priori	ty										
	Box No. III Non-	stablishment of opinion with	h regard to novelty, inventive step and industrial applicability									
	Box No. IV Lack	of unity of invention										
	Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement											
	Box No. VI Certain documents cited											
	Box No. VII Certain defects in the international application											
	Box No. VIII Certain observations on the international application											
Date of submi	ssion of the demand	·	Date of completion of this report									
Name and mai	ling address of the IPEA/E	P	Authorized officer									
F X			77.1 1 37									

International application No.
PCT/FR2004/050433

Box	No. I		Basis of the report		
1.			to the language, this report is based on the internation ler this item.	nal application in the language in which	it was filed, unless otherwise
		which i	port is based on translations from the original language is the language of a translation furnished for the purponternational search (Rule 12.3 and 23.1(b))	oses of:	·
		$\Box$	oublication of the international application (Rule 12.4)		
	•		nternational preliminary examination (Rule 55.2 and/		which have been for the state of
2.	recei	iving Off report): the inte	to the elements of the international application, this fice in response to an invitation under Article 14 are ernational application as originally filed/furnished scription:	тероп is vased on (replacement sheets e referred to in this report as "originai	witch move veen jurnished to the lly filed" and are not annexed to
		pages	1-9		as originally filed/furnished
		pages*	****		
		pages*		received by this Authority on	
	$\boxtimes$	the cla		-	
	لاے	nos.	1-10		as originally filed/furnished
				as amended (together with	any statement) under Article 19
		nos.*			,, unou runote 17
		nos.*			
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	$\triangle$		awings:		
		sheets			as originally filed/furnished
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ĺ	_	sheets			
		a sequ	ence listing and/or any related table(s) - see Supplem	ental Box Relating to Sequence Listing.	
3.		The ar	mendments have resulted in the cancellation of:		
			the description, pages		
			the claims, nos.		
			the drawings, sheets/figs		
			the sequence listing (specify):		
			any table(s) related to sequence listing (specify):		
4.		This r	report has been established as if (some of) the amendave been considered to go beyond the disclosure as fi	dments annexed to this report and listed led, as indicated in the Supplemental Bo	t below had not been made, since ox (Rule 70.2(c)).
			the description, pages		
			the claims, nos.		
			the drawings, sheets/figs		
			the sequence listing (specify):		
	If it		plies, some or all of those sheets may be marked "sup		

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Box	Box No. V  Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement							
1.	Statement							
	Novelty (N)	Claims _ 1-10	_ YES					
		Claims	_ NO					
	Inventive step (IS)	Claims 4, 6, 8-10	YES					
		Claims 1-3, 5, 7						
Industrial applicability (IA)		Claims 1-10	YES					
		Claims	_ NO					
2.	Citations and explanations (Rule 7	0.7)						
2.		de to the following documents:						
	D1: RUCHH	OEFT P ET AL: "Patterning curved						
	surfa	ces: Template generation by ion beam						
	proxi	mity lithography and relief transfer by						
	step	and flash imprint lithography" JOURNAL OF						
	VACUU	M SCIENCE AND TECHNOLOGY: PART B, AMERICAN						
	INSTI	TUTE OF PHYSICS. NEW YORK, US, vol. 17,						
	no. 6	, November 1999 (1999-11), pages						
	2965-	2969, XP002206574 ISSN: 0734-211X;						
	D2: US 20	03/104287 A1 (YUASA MITSUHIRO)						
	5 Jun	e 2003 (2003-06-05);						
	D3: DE 19	9 13 683 A1 (INSTITUT FUER						
	MIKRO	ELEKTRONIK STUTTGART STIFTUNG DES						
	OEFFE	NTLICHEN REC) 25 November 1999						
	(1999	-11-25);						
	D4: US-B1	-6 416 908 (JAIN KANTI ET AL) 9 July 2002						
	(2002	-07-09);						
	D5: ROGEF	S J A ET AL: "Printing, molding, and						
	near-	field photolithographic methods for						
	patte	rning organic lasers, smart pixels and						
	simpl	e circuits" SYNTH. MET. (SWITZERLAND),						
	SYNTH	ETIC METALS, 1 NOV. 2000, ELSEVIER,						
1								

Box No. V

SWITZERLAND, vol. 115, no. 1-3, 1 November 2000 (2000-11-01), pages 5-11, XP002279750 ISSN: 0379-6779;

- D6: US-B1-6 375 870 (VISOVSKY NICK J ET AL)
  23 April 2002 (2002-04-23);
- D7: US-A-5 281 511 (GERHARDT JOERGEN) 25 January 1994 (1994-01-25);

Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability;

- D8: EP-A-0 845 710 (SCHABLONENTECHNIK KUFSTEIN AG)
  3 June 1998 (1998-06-03);
- D9: ROOS N ET AL: "Nanoimprint lithography with a commercial 4 inch bond system for hot embossing" PROCEEDINGS OF THE SPIE THE INTERNATIONAL SOCIETY FOR OPTICAL ENGINEERING SPIE-INT. SOC. OPT. ENG USA, vol. 4343, 2001, pages 427-435, XP002317296 ISSN: 0277-786X.

The present application does not fulfil the requirements set forth in PCT Article 33(1) because the subject matter of independent claim 1 does not involve an inventive step as defined in PCT Article 33(3).

Document D1 describes a method for forming an embossing mask, characterised by the curved surface of said mask. The original mask used to define the raised structure on said mask is of a type routinely used in charged-particle lithography methods. Such a mask consists of a planar membrane that includes holes through which the particles pass. The image defined by the holes is thus transferred (imparted) to a light-sensitive resin on the curved surface. The surface is subsequently etched using the resin pattern as an etching mask.

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Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

It follows that said document includes the following features of the first claim:

- a curved lithography mask (of the "soft lithography" kind) is produced;
- a pattern is formed on a first planar mask; and
- said pattern is transferred onto a curved surface by means of lithographic projection.

D1 and the wording of the first claim differ by virtue of the specific substrate that is used for the planar mask, namely a silicon-on-insulator structure (SOI).

It should, however, be noted that the use of an SOI substrate in the production of thin-membrane masks for X-ray or particle photolithography is relatively commonplace. Documents D2 and D3 both illustrate the prior art relating to the production of such masks. Even though D1 does not disclose the exact type of mask used, it would be obvious to a person skilled in the art that the method per se is in no way dependent on the type of substrate used and that the selection of SOI is one of a plurality of obvious options. As a result, no inventive step can be recognised for the subject matter of claim 1.

The interpretation of the term "transfer" is discussed in more detail in Box VIII hereinafter.

Since a pattern can be transferred in various manners, claim 1 is not precise and includes a whole range of transfer methods.

Many conventional printing, embossing or other methods

Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

can be cited as involving a transfer of an image or pattern in accordance with the described method, irrespective of the type of material used to produce the initial pattern on the planar mask. In this regard, see documents D4-D8.

Dependent claims 2, 3, 5 and 7 do not contain any features that could contribute to an inventive step because the features disclosed therein correspond to standard practices in the production of masks in general.

However, claim 4, particularly in conjunction with claim 3, enables a clear distinction to be made between the method disclosed in the description and those described in the prior art and can be used as the basis for an inventive step. It would not be obvious for a person skilled in the art to produce a mask such as the one described, for example, in D9 and subsequently impart a non-planar configuration thereto by transferring same onto a new substrate. The preparation of a curved high-resolution mask by physically transferring the membrane/planar SOI mask pattern assembly onto a curved substrate is considered to be a non-obvious alternative to the system proposed in D9. An amended independent claim 1 should specify the exact nature of such a transfer of the resulting pattern onto the SOI mask.

Independent claim 8 describes a lithography mask that has different structural elements to the masks described in the prior art but is structurally similar to the mask described in D4 even though the latter is rigid and planar. No such silicon, silica or nitride substrate,

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Box No. VIII Certain observations on the international application

The following observations on the clarity of the claims, description, and drawings or on the question whether the claims are fully supported by the description, are made:

The wording of claim 1 is vague and open to a plurality of interpretations.

In the French text, the term "report" (herein translated as "transfer") can be interpreted in a variety of manners. It can refer to a physical transfer of a "solid" pattern from one substrate to another or to a reproduction either without physical transfer of the original or with transfer of a portion thereof, for example, a surface portion thereof (by means, for example, of lithographic projection and printing methods, by using the original as a stencil, etc.).

The term "patterns (10)" in claim 8 probably refers to the patterns with no reference signs in figure 4 and to elements (22) in figure 5.

Some of the figures are difficult to interpret because the reference signs used are incoherent. According to figure 4, element "20" denotes the mask yet, according to figure 5, "20" denotes a layer in said mask. The reference signs used for the patterns which are, according to the description, physically transferred change from "10" in figures 2 and 3 to "22" thereafter.

Physical units SI should be used (psi is used on page 9, line 18).